UMW BTA12

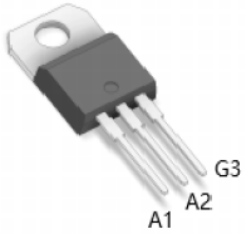
1.Description

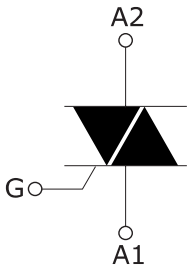
NPNPN five-layer structure of silicon bidirectional devices; with independent intellectual property rights of single-sided digging technology, table glass passivation process; multi-layer metallized electrodes on the back; with high blocking voltage and high temperature stability.

2.Features

vacuum cleaners, power tools and other motor speed controllers; solid state relays; heating controllers (temperature regulation); other phase control circuits.

3.Pinning Information





TO-220A

4.Absolute maximum ratings (T_J=25°C unless otherwise stated)

Parameter			Symbol	Values	Units
RMSon-statecurrent(full sine wave)	BTA	T_C=80°C	$I_{T(RMS)}$	12	A
Non repetitive surge peakon-state current (full cycle,T_J initial=25°C)	F=50HZ, tp=20ms		I_{TSM}	120	A
I^2t value for fusing	tp=10ms		I^2t	72	A^2S
Critical rate of rise of on-state current I_G=2 x $I_{GT,}$ tr≤100ns	T_J=125		di/dt	50	A/us
Off state repetitive peak voltage Reverse repetitive peak voltage	T_J=25°C		V_{DRM}/V_{RRM}	600/800	V
Peak gate current	tp=20us	T_J=150°C	I_{GM}	4	A
Average gate power dissipation		T_J=150°C	$P_{G(AV)}$	1	W
Storage junction temperature range			T_{STG}	-40 to 150	°C
Operating junction temperature range			T_J	-40 to 125	°C

5.1 Electrical characteristics (3 quadrants)

Parameter	Quadrant	Range	Symbol	Values				Units
V_D=12V R_L=100Ω	Ⅰ Ⅱ Ⅲ	MAX	I_{GT}	BW	CW	SW	TW	mA
		MAX		50	35	10	5	mA
		MAX	V_{GT}	1.5				V
V_D=V_{DRM}, R_L=3.3kΩ , T_J=125°C		MIN	V_{GD}	0.2				V
I_T=100mA		MAX	I_H	60	40	20	15	mA
I_G=1.2 x I_{GT}		MAX	I_L	100	60	40	30	mA
V_D = 67% V_{DRM}, gate open,mA, T_J=125°C		MIN	dv/dt	500	500	200	100	V/us
Critical rise rate of commutation voltage T_J=150°C		MIN	(dv/dt)c	8				V/us

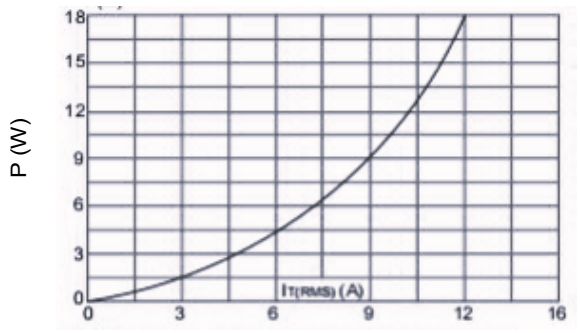
5.2 Electrical characteristics (4 quadrants)

Parameter	Quadrant	Range	Symbol	Values		Units
				B	C	
V_D=12V R_L=100Ω	Ⅰ - Ⅱ - Ⅲ	MAX	I_{GT}	50	20	mA
	Ⅳ	MAX		100	60	mA
	ALL	MAX	V_{GT}	1.5		V
V_D=V_{DRM}, R_L=3.3kΩ , T_J=125°C	ALL	MIN	V_{GD}	0.2		V
I_T=500mA		MAX	I_H	60	50	mA
I_G=1.2 x I_{GT}	Ⅰ - Ⅱ - Ⅲ	MAX	I_L	60	50	mA
	Ⅳ	MAX		100	80	mA
V_D = 67% V_{DRM}, gate open,mA, T_J=125°C		MIN	dv/dt	500		V/us
Critical rise rate of commutation voltage T_J=150°C		MIN	(dv/dt)c	10		V/us

6.Static Parameters

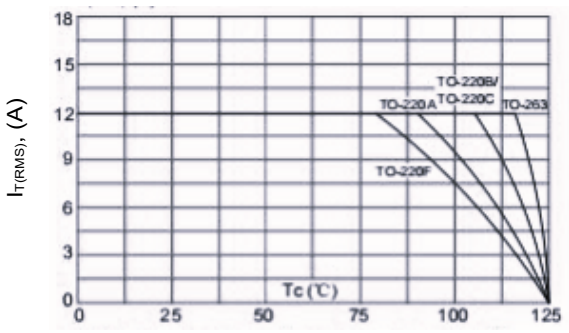
Parameter			Symbol	Values	Units
I_{TM}=24A	T_J=25°C	MAX	V_{TM}	1.5	V
threshold on-state voltage	T_J=150°C	MAX	V_{T0}	0.86	V
Dynamic resistance	T_J=150°C	MAX	Rd	36.6	mΩ
V_{DRM}=V_{RRM}	T_J=25°C	MAX	I_{DRM}, I_{RRM}	5	uA
	T_J=150°C	MAX		1	mA
Junction to ambient	BTA	MAX	$R_{th(j-c)}$	2.05	°C/W

7.Typical Characteristic



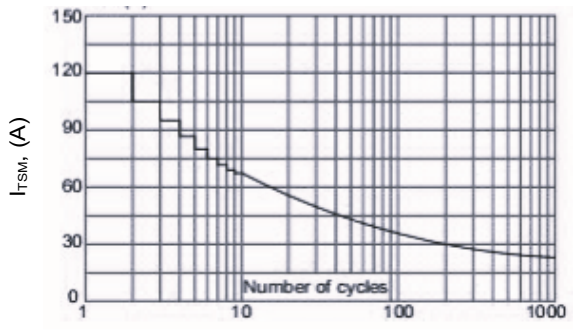
$I_{T(RMS)}$ (A)

Figure 1: Maximum power dssipation versus RMS on-state current



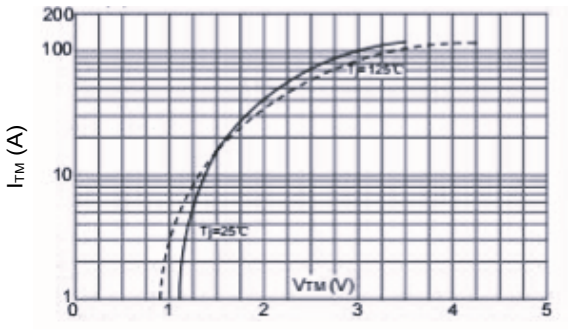
T_C (°C)

Figure 2: RMS on-slale curent versus case temperature



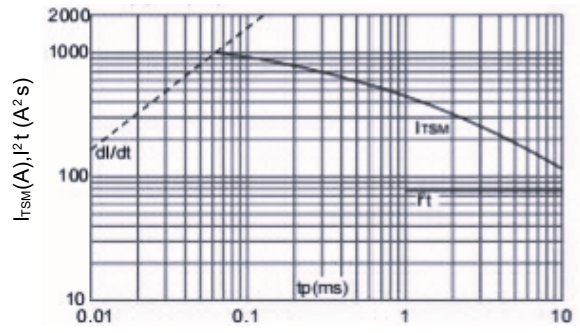
Pulse width tp(s) (for T0-220)

Figure 3: Surge peak on-stale current versus number of cycles



On-state voltage drop V_{TM}(V)

Figure 4: On-state characteristics (maximum values)



Number of full-wave cycles at 50 Hz

Figure 5: Non-repetitive surge peak on-state currentfor a sinusoidal pulse with width tp<10ms

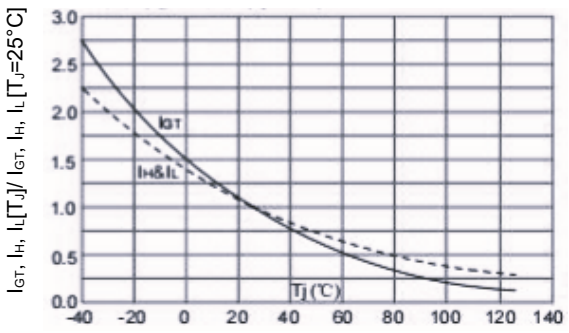
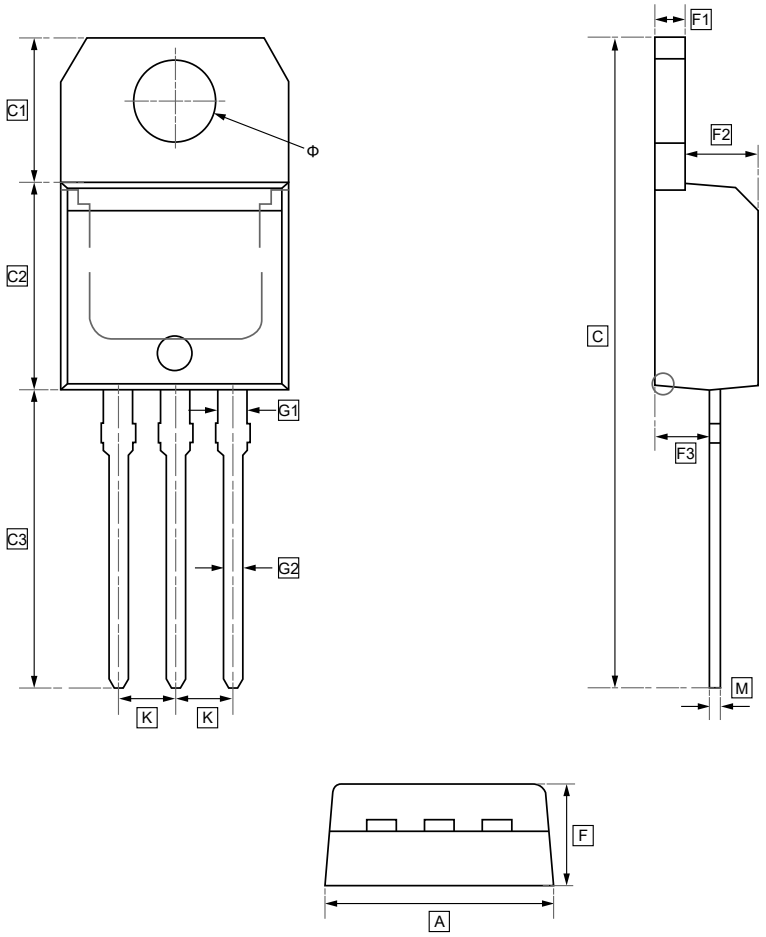


Figure 6: Relative variations of gate trigger current, hoiding curent and latching current versus

8.TO-220 Package Outline Dimensions

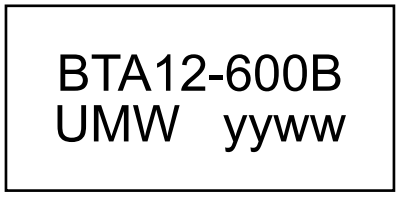


DIMENSIONS (mm are the original dimensions)

Symbol	A	C	C1	C2	C3	Φ	F	F1	F2	F3	G1	G2
Min	10.000	28.700	6.400	9.040	13.160	3.700	4.350	1.220	3.130	2.300	1.220	0.750
Max	10.200	29.100	6.500	9.240	13.460	3.800	4.650	1.320	3.330	2.700	1.320	0.850

Symbol	M	K
Min	0.450	2.540
Max	0.550	

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Marking	Package	Base QTY	Delivery Mode
UMW BTA12-600BRG	BTA12-600B	TO-220A	1000	Tube and box
UMW BTA12-600BWRG	BTA12-600BW	TO-220A	1000	Tube and box
UMW BTA12-600CRG	BTA12-600C	TO-220A	1000	Tube and box
UMW BTA12-600CWRG	BTA12-600CW	TO-220A	1000	Tube and box
UMW BTA12-600SWRG	BTA12-600SW	TO-220A	1000	Tube and box
UMW BTA12-600TWRG	BTA12-600TW	TO-220A	1000	Tube and box
UMW BTA12-800BRG	BTA12-800B	TO-220A	1000	Tube and box
UMW BTA12-800BWRG	BTA12-800BW	TO-220A	1000	Tube and box
UMW BTA12-800CRG	BTA12-800C	TO-220A	1000	Tube and box
UMW BTA12-800CWRG	BTA12-800CW	TO-220A	1000	Tube and box
UMW BTA12-800SWRG	BTA12-800SW	TO-220A	1000	Tube and box

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